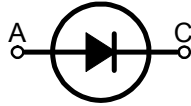
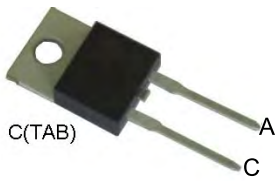


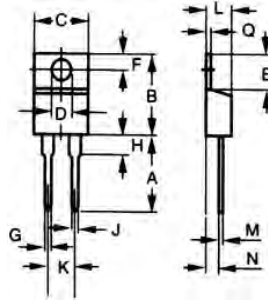
# MBR540

## High T<sub>jm</sub> Low IRRM Schottky Barrier Diodes



A=Anode, C=Cathode, TAB=Cathode

Dimensions TO-220AC



| Dim. | Inches |       | Millimeter |       |
|------|--------|-------|------------|-------|
|      | Min.   | Max.  | Min.       | Max.  |
| A    | 0.500  | 0.580 | 12.70      | 14.73 |
| B    | 0.560  | 0.650 | 14.23      | 16.51 |
| C    | 0.380  | 0.420 | 9.66       | 10.66 |
| D    | 0.139  | 0.161 | 3.54       | 4.08  |
| E    | 2.300  | 0.420 | 5.85       | 6.85  |
| F    | 0.100  | 0.135 | 2.54       | 3.42  |
| G    | 0.045  | 0.070 | 1.15       | 1.77  |
| H    | -      | 0.250 | -          | 6.35  |
| J    | 0.025  | 0.035 | 0.64       | 0.89  |
| K    | 0.190  | 0.210 | 4.83       | 5.33  |
| L    | 0.140  | 0.190 | 3.56       | 4.82  |
| M    | 0.015  | 0.022 | 0.38       | 0.56  |
| N    | 0.080  | 0.115 | 2.04       | 2.49  |
| Q    | 0.025  | 0.055 | 0.64       | 1.39  |

|               | V <sub>RRM</sub> | V <sub>RMS</sub> | V <sub>DC</sub> |
|---------------|------------------|------------------|-----------------|
|               | V                | V                | V               |
| <b>MBR540</b> | 40               | 28               | 40              |

| Symbol           | Characteristics   | Maximum Ratings | Unit |
|------------------|---|-----------------|------|
| I <sub>AV</sub>  | Maximum Average Forward Rectified Current @T <sub>c</sub> =95°C   | 5               | A    |
| I <sub>FSM</sub> | Peak Forward Surge Current 8.3ms Single Half-Sine-Wave Superimposed On Rated Load (JEDEC METHOD)        | 175             | A    |
| V <sub>F</sub>   | Maximum Forward Voltage At 5.0A DC (Note 1)   | 0.55            | V    |
| I <sub>R</sub>   | Maximum DC Reverse Current @T <sub>J</sub> =25°C<br>At Rated DC Blocking Voltage @T <sub>J</sub> =125°C | 0.5<br>33       | mA   |
| C <sub>J</sub>   | Typical Junction Capacitance (Note 2)   | 350             | pF   |
| R <sub>θJC</sub> | Typical Thermal Resistance (Note 3)   | 3.5             | °C/W |
| T <sub>J</sub>   | Operating Temperature Range   | -55 to +125     | °C   |
| T <sub>stg</sub> | Storage Temperature Range   | -55 to +150     | °C   |

NOTES: 1. 300us Pulse Width, 2% Duty Cycle.  
2. Measured At 1.0MHz And Applied Reverse Voltage Of 4.0V DC.  
3. Thermal Resistance Junction To Case.

### FEATURES

- \* Metal of silicon rectifier, majority carrier conduction
- \* Guard ring for transient protection
- \* Low power loss, high efficiency
- \* High current capability, low V<sub>F</sub>
- \* High surge capacity
- \* For use in low voltage, high frequency inverters, free whelling, and polarity protection applications
- \* RoHS compliant

### MECHANICAL DATA

- \* Case: TO-220AC molded plastic
- \* Polarity: As marked on the body
- \* Weight: 2 grams
- \* Mounting position: Any



# MBR540

## High T<sub>jm</sub> Low IRRM Schottky Barrier Diodes

FIG.1 - FORWARD CURRENT DERATING CURVE

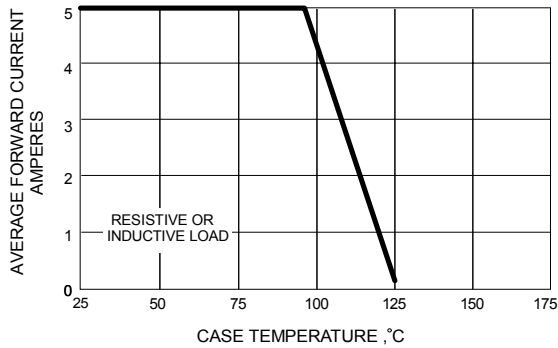


FIG.2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

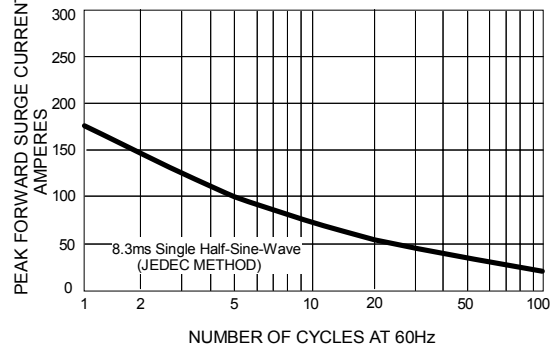


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

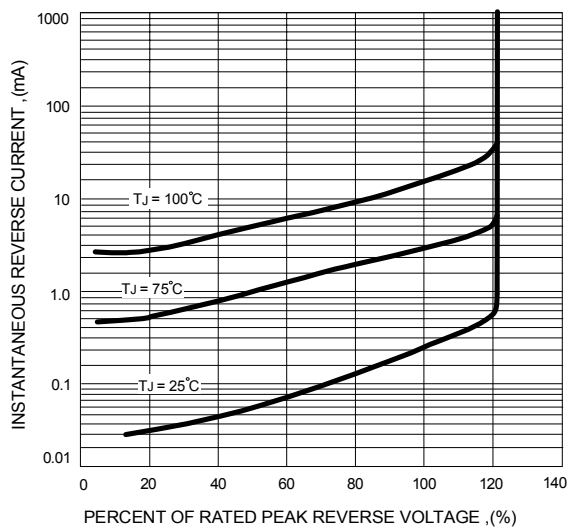


FIG.4 - TYPICAL FORWARD CHARACTERISTICS

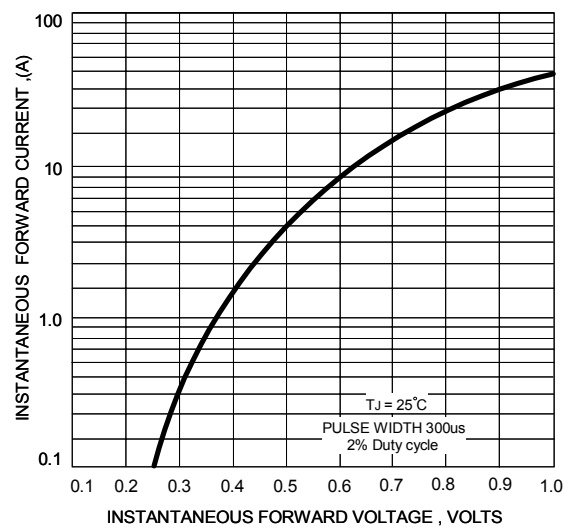


FIG.5 - TYPICAL JUNCTION CAPACITANCE

